

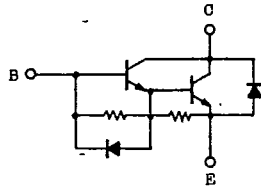
9097250 TOSHIBA (DISCRETE/OPTO)

90D 16279 DT-33-35

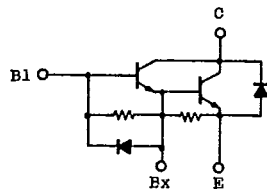


**SEMICONDUCTOR**  
TECHNICAL DATA

MG200H1AL2  
MG200H1FL1A

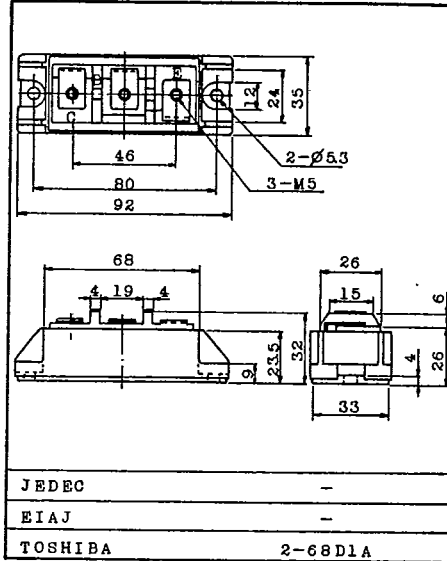


MG200H1AL2



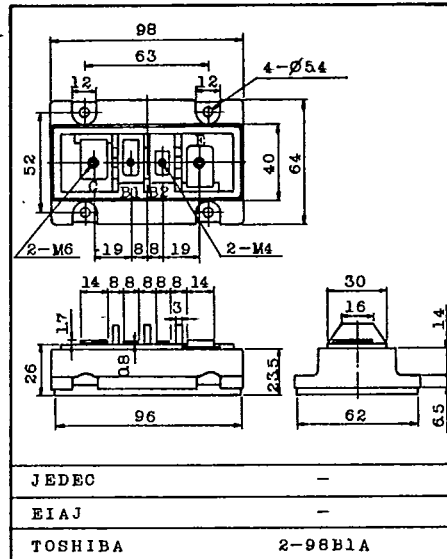
MG200H1FL1

Unit in mm



Weight : 210g

Unit in mm



Weight : 420g

TOSHIBA CORPORATION

GT1A2A

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16280

DT-33-35



# SEMICONDUCTOR

## TECHNICAL DATA

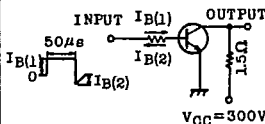
MG200H1AL2  
MG200H1FL1A

MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CB10}$	600	V
Collector-Emitter Voltage	$V_{CEO}$	600	V
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	550	V
Emitter-Base Voltage	$V_{EB10}$	6	V
Collector Current	DC	$I_C$	200
	1ms	$I_C$	400
	DC	$-I_C$	200
Base Current	$I_{B1}$	8	A
Collector Power Dissipation ( $T_c=25^\circ\text{C}$ )	$P_C$	800	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-40~125	$^\circ\text{C}$
Isolation Voltage	$V_{isol}$	2500 (AC 1 Minute)	V
Screw Torque (Terminal M4/M6/Mounting)	-	20/30/30	kg·cm

ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CB10}$	$V_{CB1}=600\text{V}, I_E=0$	-	-	2.0	mA
Emitter Cut-off Current	$I_{EB10}$	$V_{EB1}=6\text{V}, I_C=0$	-	-	400	mA
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C=0.5\text{A}, L=40\text{mH}$	550	-	-	V
DC Current Gain	$h_{FE}$	$V_{CE}=5\text{V}, I_C=200\text{A}$	80	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200\text{A}, I_{B1}=6\text{A}$	-	-	2.0	V
Base-Emitter Saturation Voltage	$V_{BE1(sat)}$		-	-	2.7	V
Emitter-Collector Voltage	$V_{ECO}$	$I_E=200\text{A}, I_{B1}=0$	-	-	1.5	V
Reverse Recovery Time	$t_{rr}$	$-I_C=200\text{A}, V_{EB1}=3\text{V}$ $V_{CE}=300\text{V}$	-	-	2.0	$\mu\text{s}$
Collector Output Capacitance	$C_{ob1}$	$V_{CB1}=50\text{V}, I_E=0$ $f=1\text{MHz}$	-	1670	-	pF
Switching Time	Turn-on Time	$t_{on}$	-	-	2.0	$\mu\text{s}$
	Storage Time	$t_{stg}$	-	-	12	
	Fall Time	$t_f$	$I_{B1}=-I_{B2}=6\text{A}$ DUTY CYCLE=0.5%	-	-	
Thermal Resistance (Junction to Case)	$R_{th(j-c)}$	Transistor	-	-	0.156	$^\circ\text{C/W}$
		Diode	-	-	0.65	



TOSHIBA CORPORATION

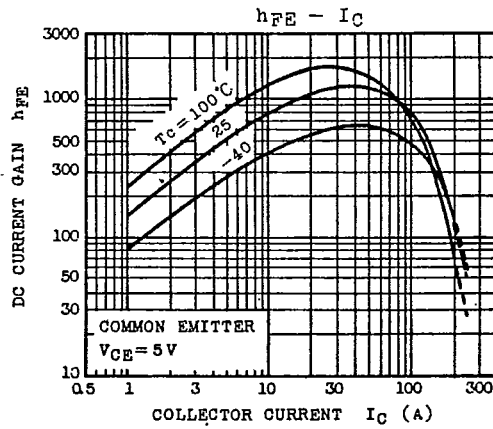
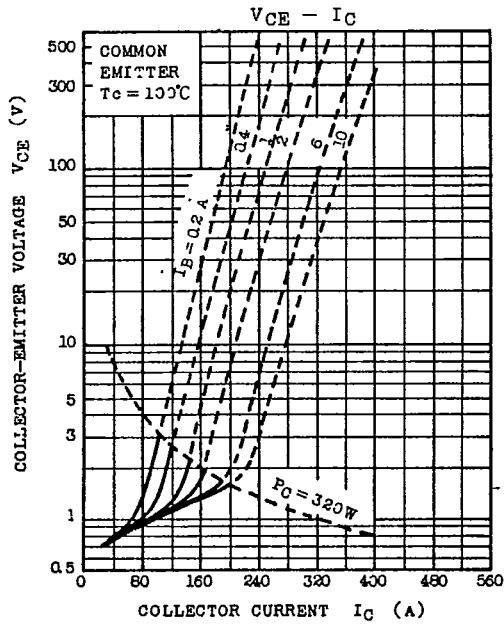
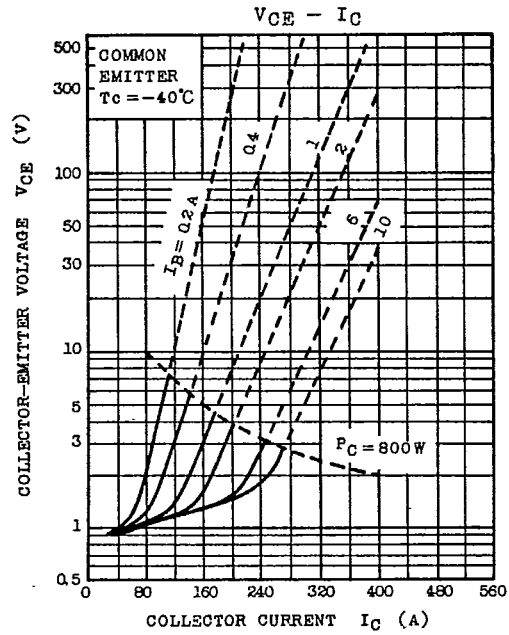
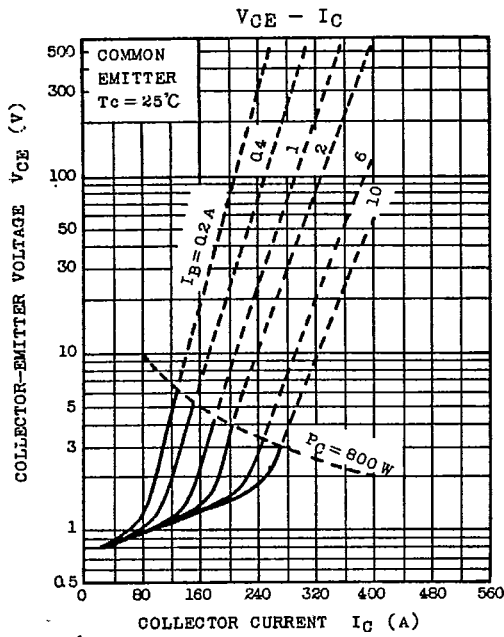
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SEMICONDUCTOR

TECHNICAL DATA

MG200H1AL2  
MG200H1FL1A



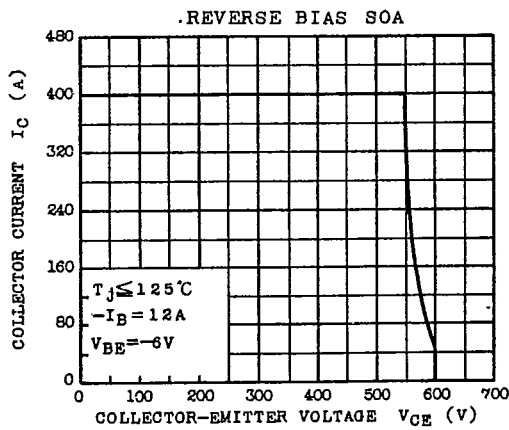
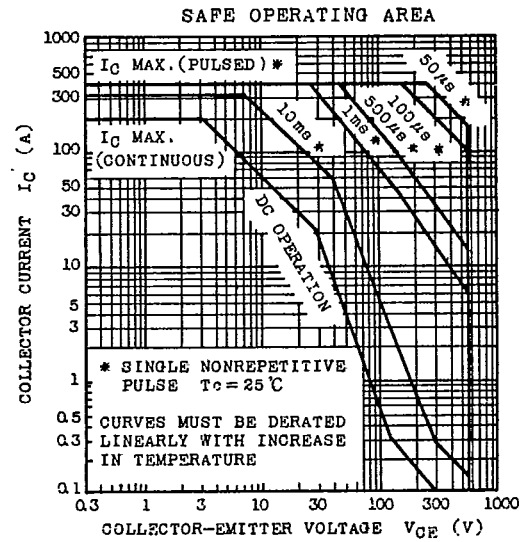
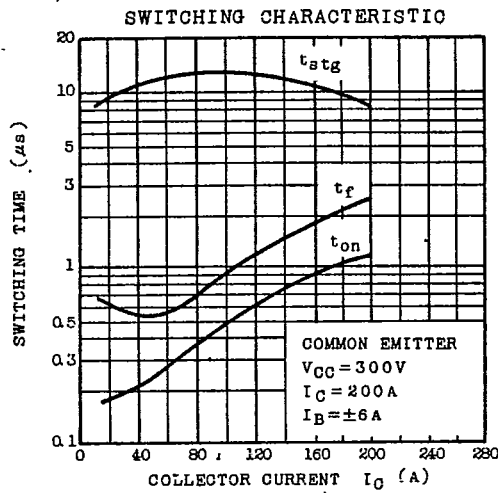
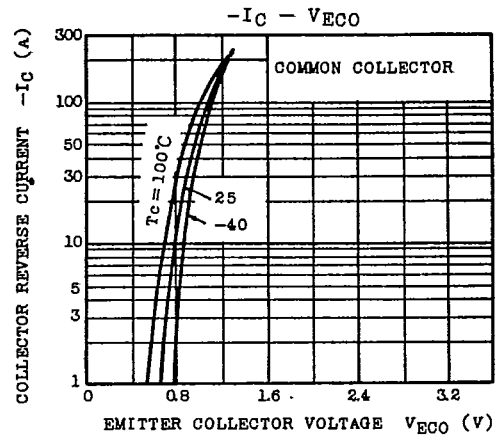
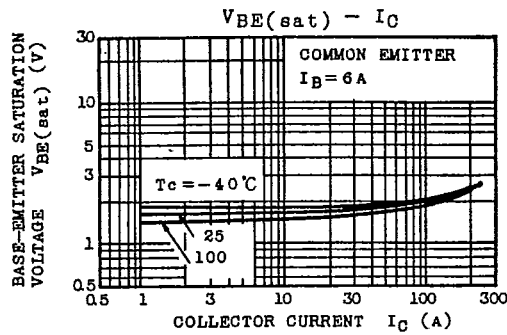
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SEMICONDUCTOR

TECHNICAL DATA

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MG200H1FL1A

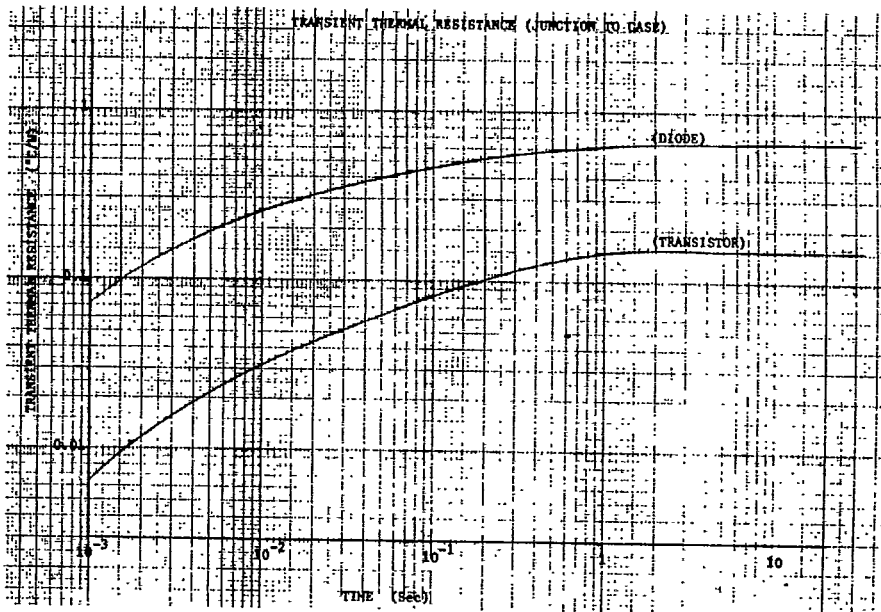
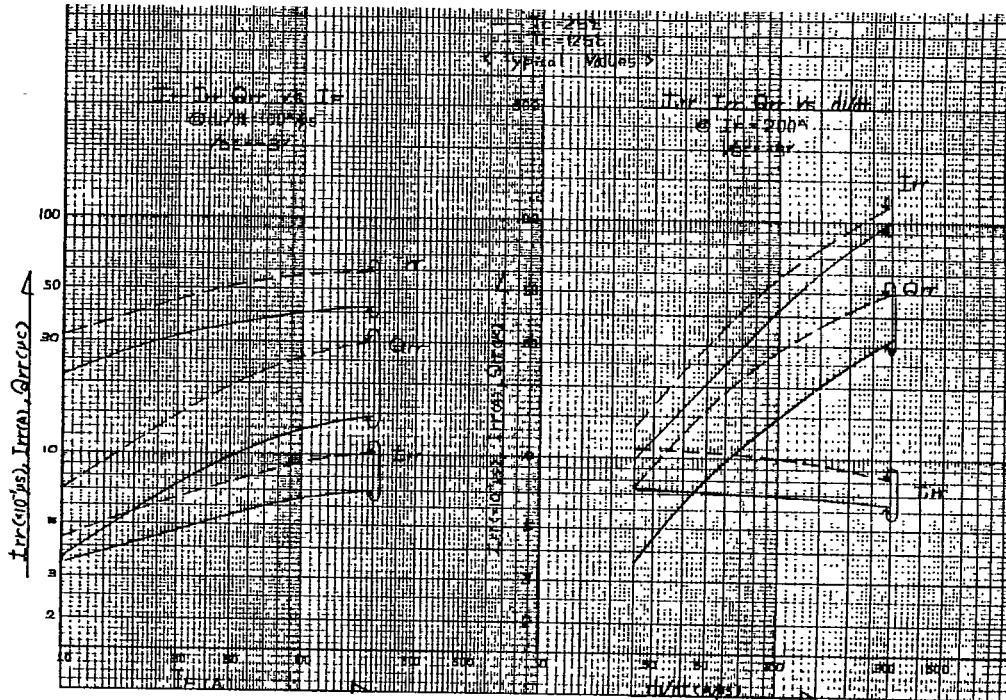


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# SEMICONDUCTOR TECHNICAL DATA

MG200H1AL2  
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TOSHIBA CORPORATION

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Datasheets for electronic components.